

line 22, change "72" to --172--.

IN THE CLAIMS:

Please amend the claims as follows:

1. (Amended) A method for manufacturing an active matrix liquid crystal device using five masks, comprising:

forming a plurality of gate electrodes over a substrate using a first mask;

forming a plurality of etch stoppers over the plurality of gate electrodes using a second mask, each etch stopper being formed over one gate electrode;

forming a plurality of drain electrodes and a plurality of source electrodes [formed] using a third mask, a portion of each of the drain electrodes being formed over a first portion of a corresponding one of the etch stoppers and a portion of each of the source electrodes being formed over a second portion of the corresponding one of the etch stoppers, wherein the source and the drain electrodes are separated over the corresponding one of the etch stoppers;

forming over the substrate a passivation layer [over the substrate] having [a plurality of] at least one first via hole[s] using a fourth mask; and

forming a pixel electrode over the passivation layer using a fifth mask.

2. The method of claim 1, further comprising:

forming a plurality of gate lines over the substrate using the first mask;

forming a gate insulating layer over the substrate and the plurality of gate lines, wherein the passivation layer